

Description

The SD3314A is a step-down constant current LED driver. When the input voltage down to lower than LED forward voltage, then SD3314A run into LDO mode.

The SD3314A supports a range of input voltages from 2.5V to 6.0V, allowing the use of a single Li+/Li-polymer cell, 3AA or 4AA cell, USB, and other standard power sources.

The FB voltage is only 0.1V to achieve high efficiency.

SD3314A employ internal power switch and synchronous rectifier to minimize external part count and realize high efficiency.

During shutdown, the input is disconnected from the output and the shutdown current is less than 1µA. Other key features include under-voltage lockout to prevent deep battery discharge of the Li+ battery.

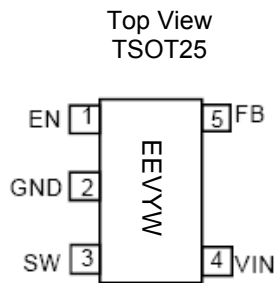
Features

- Efficiency up to 93%
- 180µA(typ) Quiescent Current
- Output Current: Up to 1A
- Internal Synchronous Rectifier
- 1.5MHz Switching Frequency
- Soft-Start
- Under-Voltage Lockout
- Short LED Protection
- Open LED Protection
- Thermal Shutdown
- 5-Pin Small TSOT25 Packages
- Pb-Free Package

Applications

- 3AA or 4AA Batteries Powered Flashlight
- 1 Cell Li-Ion Battery Powered Flashlight

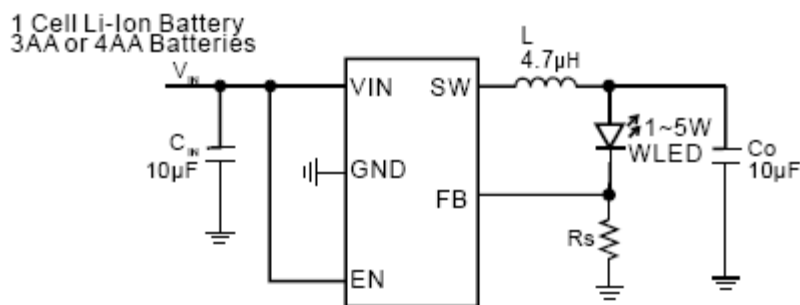
Pin Assignments



EE: Product Code
of SD3314A
V: Internal Code
Y: Year
W: Week

Marking Information

Typical Applications Circuit

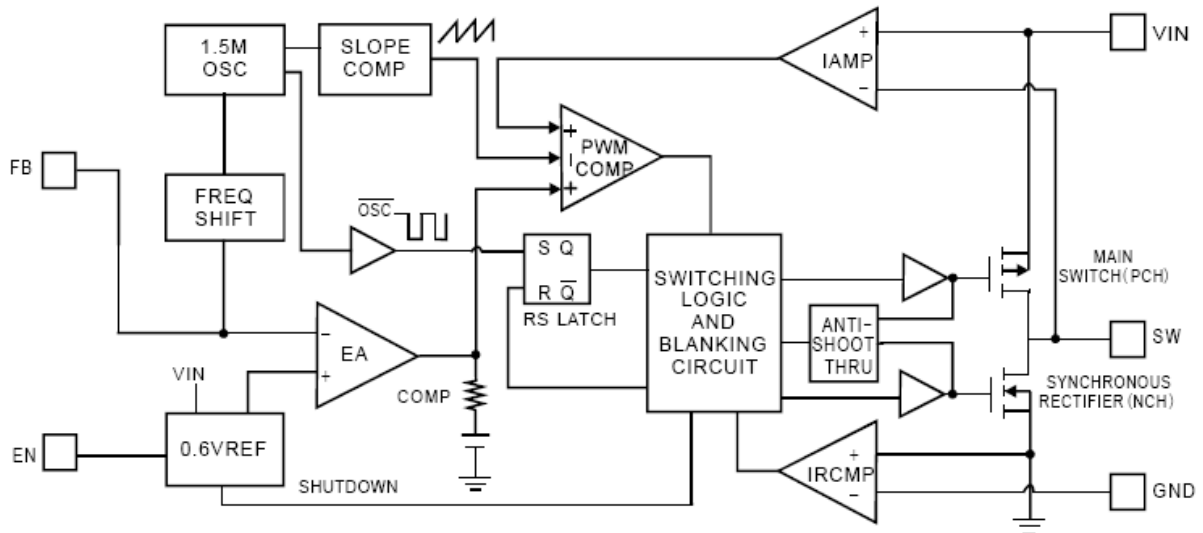


$$I_{LED} = 0.1/R_s$$

Pin Description

Pin Number	Pin Name	Function
1	EN	Enable control input. Force this pin voltage above 1.5V, enables the chip, and below 0.3V shuts down the device.
2	GND	Ground
3	SW	The drains of the internal main and synchronous power MOSFET.
4	VIN	Chip main power supply pin.
5	FB	Feedback voltage to internal error amplifier, the threshold voltage is 0.1V.

Block Diagram



Absolute Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

These are stress ratings only and functional operation is not implied. Exposure to absolute maximum ratings for prolonged time periods may affect device reliability. All voltages are with respect to ground.

Parameter	Rating	Unit
Input Pin Voltage	-0.3 to +6.5	V
EN, FB Pin Voltage	-0.3 to V_{IN}	
SW Pin Voltage	-0.3 to ($V_{IN} + 0.3$)	
Junction Temperature Range	150	$^\circ\text{C}$
Storage Temperature Range	-65 to +150	
Soldering Temperature	300, 5sec	

Recommended Operating Conditions (@T_A = +25°C, unless otherwise specified.)

Parameter	Rating	Unit
Supply Voltage	2.5 to 6.0	°C
Operation Temperature Range	-40 to +85	
Junction Temperature Range	-40 to +125	

Thermal Information

Parameter	Symbol	Package	Max	Unit
Thermal Resistance (Junction to Case)	θ_{JC}	TSOT25 (Note 1)	130	°C/W
Thermal Resistance (Junction to Ambient)	θ_{JA}	TSOT25	250	
Internal Power Dissipation	P _D	TSOT25	400	mW

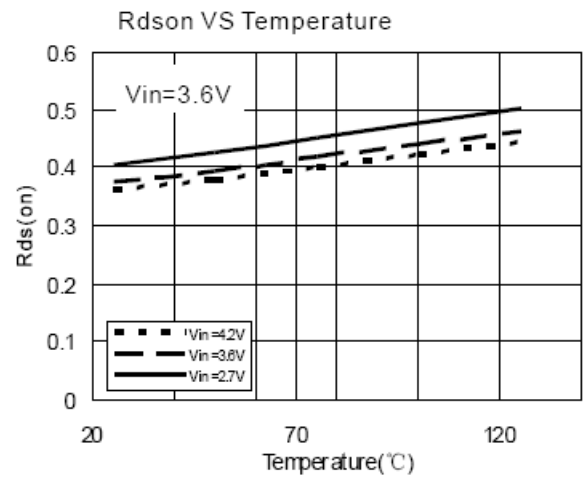
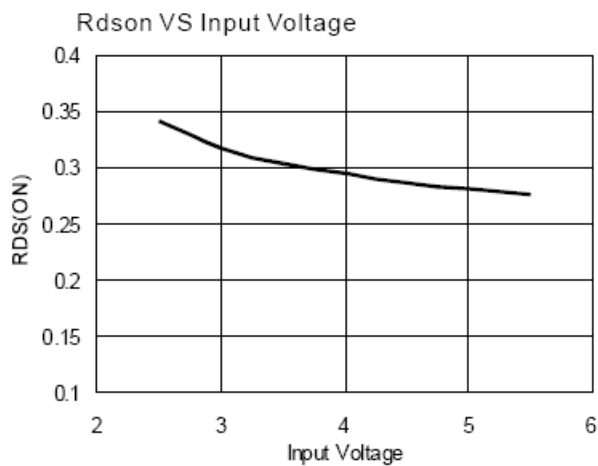
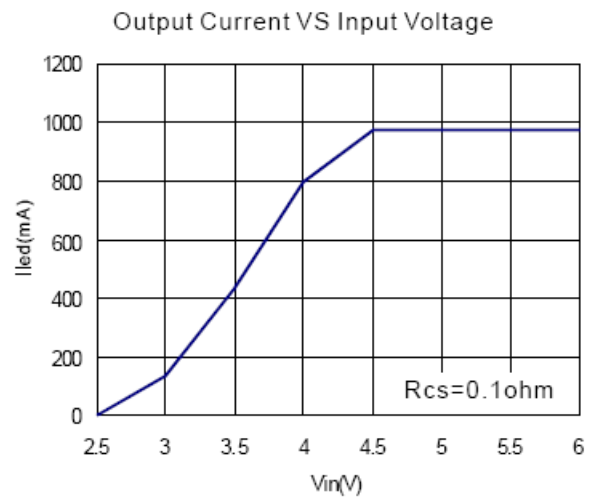
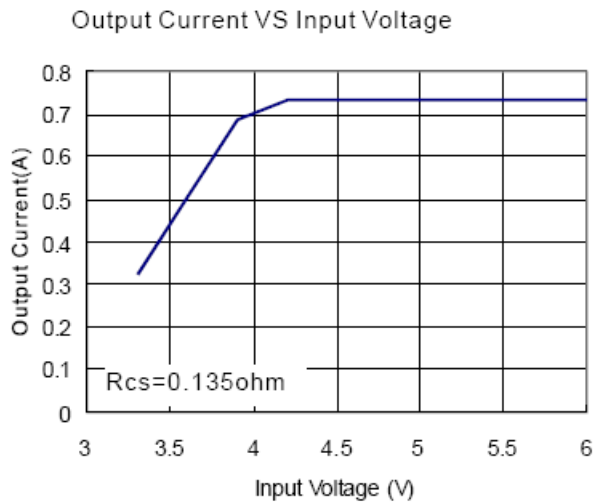
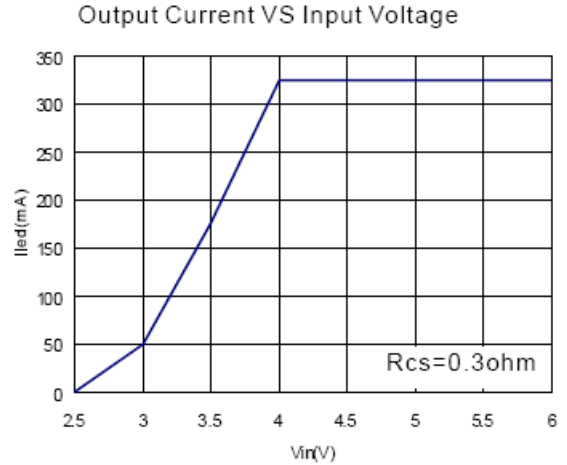
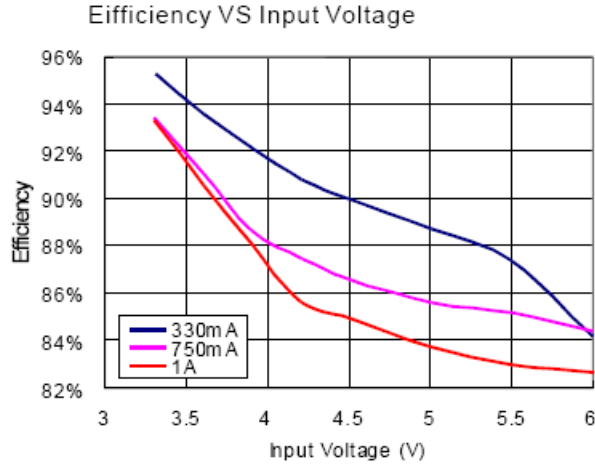
Note: 1. The maximum output current for TSOT25 package is limited by internal power dissipation capacity as described in Application Information herein after.

Electrical Characteristics

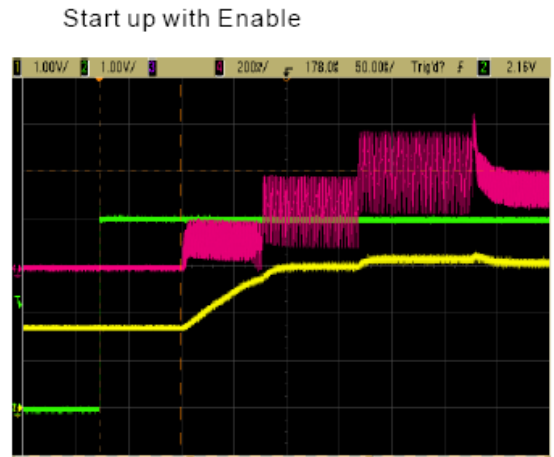
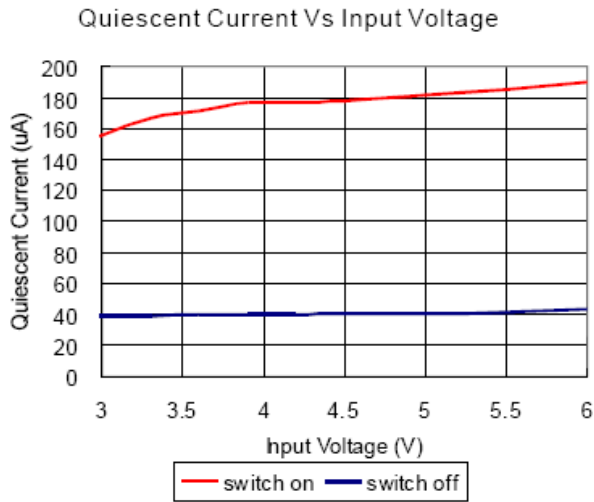
(@T_A = +25°C, V_{IN} = 4.2V, Real WLED load, L = 4.7μH, C_{IN} = 10μF, C_O = 10μF, unless otherwise specified.)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Units
Input Voltage Range	V _{IN}		2.5		6.0	V
Regulated Feedback Voltage	V _{FB}		0.095	0.100	0.105	V
Peak Inductor Current	I _{PK}	V _{IN} = 5V		1.5		A
Quiescent Current	I _Q	No Load		180		μA
Shutdown Current	I _{SD}	V _{EN} = 0V			1	μA
Oscillator Frequency	f _{OSC}	V _O = 100%	1.2	1.5	1.8	MHz
Drain-Source On-State Resistance	R _{DS(ON)}	I _{DS} = 100mA	P MOSFET	0.30	0.45	Ω
			N MOSFET	0.35	0.50	Ω
SW Leakage Current	I _{LSW}			±0.01	1	μA
High Efficiency	η			93		%
EN Threshold High	V _{EH}		1.5			V
EN Threshold Low	V _{EL}				0.3	V
EN Leakage Current	I _{EN}			±0.01		μA
Over Temperature Protection	OTP			150		°C
OTP Hysteresis	OTH			30		°C

Typical Performance Characteristics (@ $T_A = +25^\circ\text{C}$, $L = 4.7\mu\text{F}$, $C_{IN} = 10\mu\text{F}$, $C_O = 10\mu\text{F}$, unless otherwise specified.)



Typical Performance Characteristics (cont.) @ $T_A = +25^{\circ}\text{C}$, $L = 4.7\mu\text{F}$, $C_{IN} = 10\mu\text{F}$, $C_O = 10\mu\text{F}$, unless otherwise specified.)



Application Information

The basic SD3314A application circuit is shown in Page 1. External component selection is determined by the load requirement, selecting L first and then C_{IN} and C_{OUT}.

Inductor Selection

For most applications, the value of the inductor will fall in the range of 1μH to 4.7μH. Its value is chosen based on the desired ripple current. Large value inductors lower ripple current and small value inductors result in higher ripple currents. Higher V_{IN} or V_{OUT} also increases the ripple current as shown in equation 1. A reasonable starting point for setting ripple current is ΔI_L = 400mA (40% of 1A).

$$\Delta I_L = \frac{1}{(f)(L)} V_{OUT} \left(1 - \frac{V_{OUT}}{V_{IN}} \right) \quad \text{Equation (1)}$$

The DC current rating of the inductor should be at least equal to the maximum load current plus half the ripple current to prevent core saturation. Thus, a 1.4A rated inductor should be enough for most applications (1A + 400mA). For better efficiency, choose a low DC-resistance inductor.

Using Ceramic Input Output Capacitors

Higher values, lower cost ceramic capacitors are now becoming available in smaller case sizes. Their high ripple current, high voltage rating and low ESR make them ideal for switching regulator applications. Using ceramic capacitors can achieve very low output ripple and small circuit size.

When choosing the input and output ceramic capacitors, choose the X5R or X7R dielectric formulations. These dielectrics have the best temperature and voltage characteristics of all the ceramics for a given value and size.

Thermal Consideration

Thermal protection limits power dissipation in the SD3314A. When the junction temperature exceeds +150°C, the OTP (Over Temperature Protection) starts the thermal shutdown and turns the pass transistor off. The pass transistor resumes operation after the junction temperature drops below +120°C.

For continuous operation, the junction temperature should be maintained below +125°C. The power dissipation is defined as:

$$P_D = I_O^2 \frac{V_O R_{DS(ON)H} + (V_{IN} - V_O) R_{DS(ON)L}}{V_{IN}} + (t_{SW} F_S I_O + I_Q) V_{IN}$$

I_Q is the step-down converter quiescent current. The term t_{sw} is used to estimate the full load step-down converter switching losses.

For the condition where the step-down converter is in dropout at 100% duty cycle, the total device dissipation reduces to:

$$P_D = I_O^2 R_{DS(ON)H} + I_Q V_{IN}$$

Since R_{DS(ON)}, quiescent current, and switching losses all vary with input voltage, the total losses should be investigated over the complete input voltage range. The maximum power dissipation depends on the thermal resistance of IC package, PCB layout, the rate of surrounding airflow and temperature difference between junction and ambient. The maximum power dissipation can be calculated by the following formula:

$$P_D = \frac{T_{J(MAX)} - T_A}{\theta_{JA}}$$

Where T_{J(MAX)} is the maximum allowable junction temperature +125°C. T_A is the ambient temperature and θ_{JA} is the thermal resistance from the junction to the ambient. Based on the standard JEDEC for a two layers thermal test board, the thermal resistance θ_{JA} of TSOT25 package is 250°C/W. The maximum power dissipation at T_A = +25°C can be calculated by following formula:

$$P_D = (125^\circ\text{C} - 25^\circ\text{C}) / 250^\circ\text{C} / \text{W} = 0.4\text{W}$$

Application Information

Setting the Output Current

The internal feedback(FB) voltage is 0.1V (Typical). The output current is calculated as below:

$$I_{LED} = 0.1 / R_S$$

The output Current is given by the following table.

$R_S(\Omega)$	$I_{LED}(mA)$
0.286	350
0.143	700
0.1	1000

As the input voltage approaches the LED forward voltage, the SD3314A turns the P-Channel transistor continuously on. In this mode the Voltage drop on LED is equal to the input voltage minus the voltage drop across the P-Channel transistor, Inductor and current resistor:

$$V_{LEDDROP} = V_{IN} - I_{LED}(R_{DS(ON)} + R_L + R_S)$$

where $R_{DS(ON)}$ = P-Channel switch ON resistance, I_{LED} = LED current, R_L = Inductor DC Resistance, R_S = Inductor DC Resistance.

Thermal Shutdown

When the die temperature exceeds +150°C, a reset occurs and the reset remains until the temperature decrease to +120°C, at which time the circuit can be restarted.

PCB Layout Check List

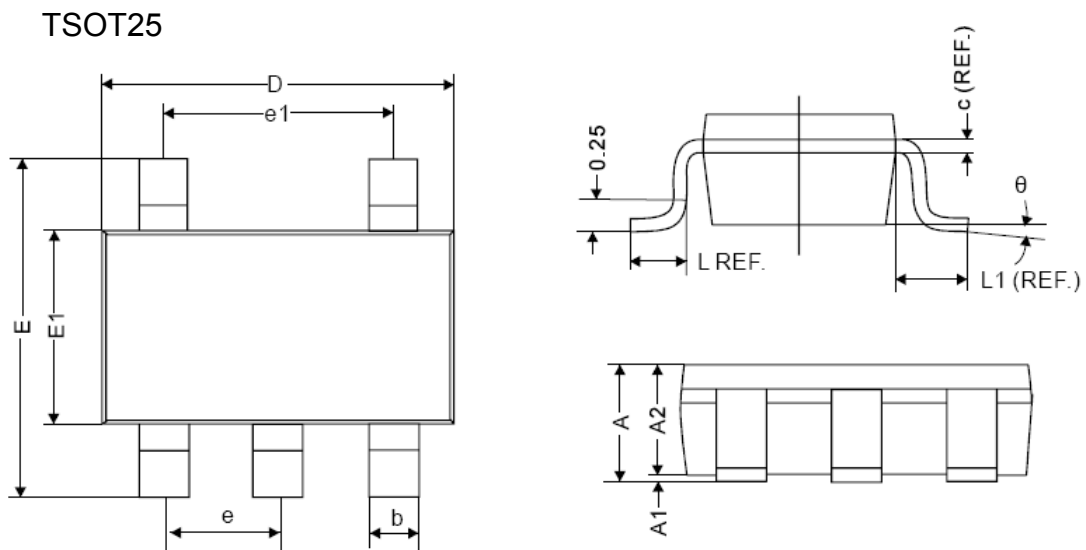
When laying out the printed circuit board, the following checklist should be used to ensure proper operation of the SD3314A. These items are also illustrated graphically in Figure 1. Check the following in your layout:

1. The power traces, consisting of the GND trace, the SW trace and the VIN trace should be kept short, direct and wide.
2. Does the V_{FB} pin connect directly to the current sense resistor? The current sense resistor to GND trace should be kept short, direct and wide.
3. Does the (+) plate of C_{IN} connect to V_{IN} as closely as possible? This capacitor provides the AC current to the internal power MOSFETs.
4. Keep the switching node, SW, away from the sensitive VFB node.
5. Keep the (-) plates of C_{IN} and C_{OUT} as close as possible.

Ordering Information

Part Number	Marking	Package Type	Standard Package
SD3314A	Refer to Marking Information Below	TSOT25	3000 Units/Tape&Reel

Package Outline Dimensions (All dimensions in mm.)



REF.	Millimeter	
	Min	Max
A	1.10 MAX	
A1	0	0.10
A2	0.70	1
c	0.12 REF.	
D	2.70	3.10
E	2.60	3.00
E1	1.40	1.80
L	0.45 REF.	
L1	0.60 REF.	
θ	0°	10°
b	0.30	0.50
e	0.95 REF.	
e1	1.90 REF.	